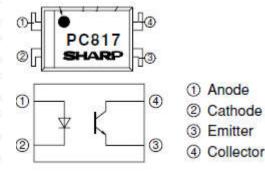


■ Electro-optical Characteristics

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	Paramete	r	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	Forward voltage		V_F	I _F =20mA		1.2	1.4	V
Input	Peak forward voltage		V_{FM}	I _{FM} =0.5A	1971	32	3.0	V
	Reverse current		IR	V _R =4V		28	10	μΑ
	Terminal capacitance		Ct	V=0, f=1kHz	1.00	30	250	pF
Output	Collector dark current		I _{CEO}	V _{CE} =50V, I _F =0		20	100	nA
	Collector-emitter breakdown voltage		BV _{CEO}	I _C =0.1mA, I _P =0	*5 80	=	-	V
	Emitter-collector breakdown voltage		BV _{ECO}	$I_{E}=10\mu A, I_{P}=0$	6	50	1754	V
Transfer characteristics	Collector current		Ic	$I_F=5mA$, $V_{CE}=5V$	2.5	=	30.0	mA
	Collector-emitter saturation voltage		V _{CE (sat)}	$I_F=20mA$, $I_C=1mA$	1975	0.1	0.2	V
	Isolation resistance		Riso	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	123	Ω
	Floating capacitance		Cf	V=0, f=1MHz	15-5	0.6	1.0	pF
	Cut-off frequency		fc	V _{CE} =5V, I _C =2mA, R _L =100Ω, -3dB		80	125	kHz
	Response time	Rise time	tr	V_{CE} =2V, I_C =2mA, R_L =100 Ω		4	18	μs
		Fall time	tr			3	18	us



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^{*5} From the production Date code "J5" (May 1997) to "P7" (July 2002), however the products were screened by BV_{CDD}≥70V.